NL7SZ58

Configurable Multifunction Gate

The NL7SZ58 is an advanced high−speed CMOS multifunction gate. The device allows the user to choose logic functions AND, OR, NAND, NOR, XOR, INVERT and BUFFER. The device has Schmitt−trigger inputs, thereby enhancing noise immunity.

The NL7SZ58 input and output structures provide protection when voltages up to 7.0 V are applied, irregardless of the supply voltage.

Features

- High Speed: t_{PD} = 3.4 ns (Typ) @ V_{CC} = 5.0 V
- Low Power Dissipation: I_{CC} = 1 μA (Maximum) at T_A = 25°C
- Power Down Protection Provided on inputs
- Balanced Propagation Delays
- Overvoltage Tolerant (OVT) Input and Output Pins
- Ultra−Small Package
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- This is a Pb−Free Device

ON Semiconductor®

http://onsemi.com

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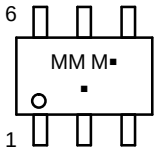
SC−88 (SOT−363)
CASE 419B

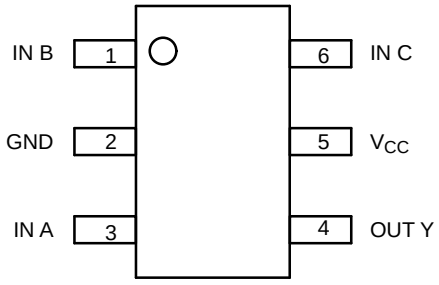
MARKING DIAGRAM



MM = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENTS



(Top View)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

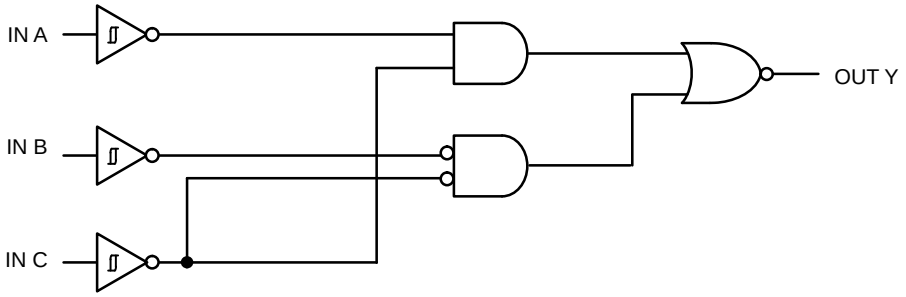


Figure 1. Function Diagram

PIN ASSIGNMENT

1	IN B
2	GND
3	IN A
4	OUT Y
5	V_{CC}
6	IN C

FUNCTION TABLE*

Input			Output
A	**B**	**C**	**Y**
L	L	L	L
L	L	H	H
L	H	L	L
L	H	H	L
H	L	L	H
H	L	H	H
H	H	L	H
H	H	H	L

*To select a logic function, please refer to “Logic Configurations section”.

LOGIC CONFIGURATIONS

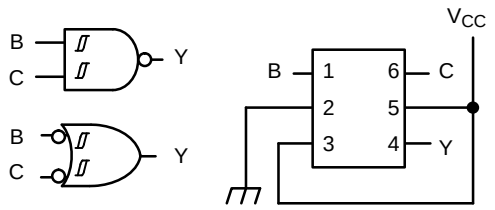


Figure 2. 2−Input NAND (When A = “H”)

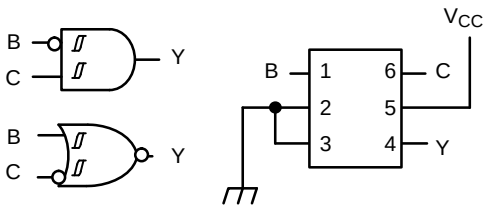


Figure 3. 2−Input AND with Input B Inverted (When A = “L”)

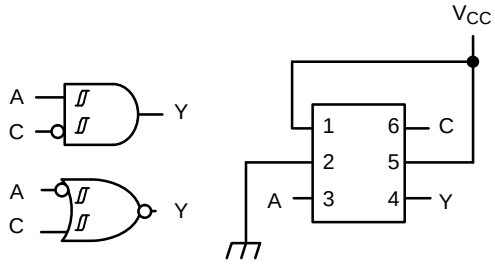


Figure 4. 2−Input AND with Input C Inverted (When B = “H”)

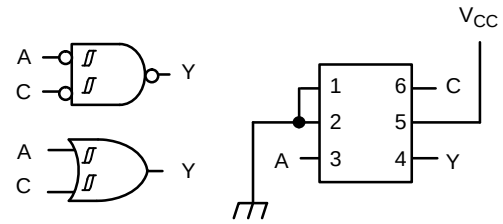


Figure 5. 2−Input OR (When B = “L”)

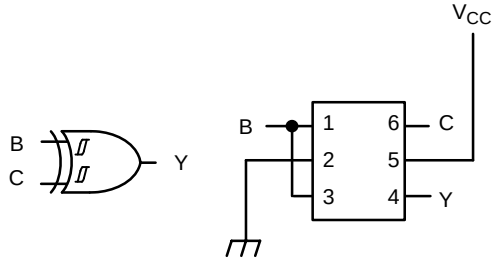


Figure 6. 2−Input XOR (When A = B)

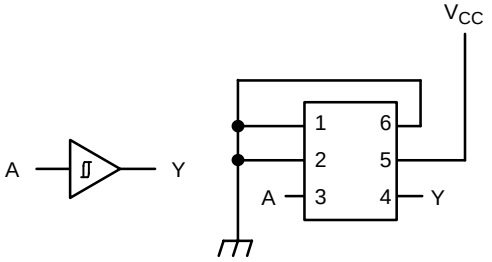


Figure 7. Buffer (When B = C = “L”)

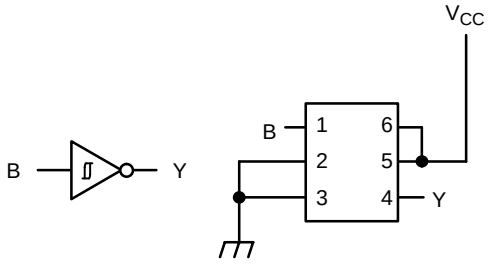


Figure 8. Inverter (When A = “L” and C = “H”)

MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_{IN}	DC Input Voltage		−0.5 to +7.0	V
V_{OUT}	DC Output Voltage		−0.5 to +7.0	V
I_{IK}	DC Input Diode Current	V_{IN} < GND	−50	mA
I_{OK}	DC Output Diode Current	V_{OUT} < GND	−50	mA
I_O	DC Output Source/Sink Current		±50	mA
I_{CC}	DC Supply Current Per Supply Pin		±100	mA
I_{GND}	DC Ground Current per Ground Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction Temperature Under Bias		+150	°C
θ_{JA}	Thermal Resistance (Note 1)	SC−88	350	°C/W
P_D	Power Dissipation in Still Air at 85°C	SC−88	200	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating Oxygen	Index: 28 to 34	UL 94 V−0 @ 0.125 in	
V_{ESD}	ESD Withstand Voltage	Human Body Mode (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 N/A	V
$I_{LATCHUP}$	Latchup Performance Above V_{CC} and Below GND at 125°C (Note 5)		±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Measured with minimum pad spacing on an FR4 board, using 10 mm−by−1 inch, 2 ounce copper trace no air flow.
2. Tested to EIA/JESD22−A114−A.
3. Tested to EIA/JESD22−A115−A.
4. Tested to JESD22−C101−A.
5. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	Positive DC Supply Voltage		1.65	5.5	V
V_{IN}	Digital Input Voltage		0	5.5	V
V_{OUT}	Output Voltage		0	5.5	V
T_A	Operating Free−Air Temperature		−55	+125	°C
$\Delta t/\Delta V$	Input Transition Rise or Fall Rate	V_{CC} = 2.5 V ± 0.2 V V_{CC} = 3.3 V ± 0.3 V V_{CC} = 5.0 V ± 0.5 V	0 0 0	No Limit No Limit No Limit	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	V_{CC} (V)	T_A = 25°C			$T_A \leq$ +85°C		T_A = −55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{T+}	Positive Threshold Voltage		1.65	0.79		1.16		1.16		1.16	V
			2.3	1.11		1.56		1.56		1.56	
			3.0	1.5		1.87		1.87		1.87	
			4.5	2.16		2.74		2.74		2.74	
			5.5	2.61		3.33		3.33		3.33	
V_{T-}	Negative Threshold Voltage		1.65	0.35		0.62	0.35		0.35		V
			2.3	0.58		0.87	0.58		0.58		
			3.0	0.84		1.19	0.84		0.84		
			4.5	1.41		1.9	1.41		1.41		
			5.5	1.78		2.29	1.78		1.78		
V_H	Hysteresis Voltage		1.65	0.30		0.62	0.30	0.62	0.30	0.62	V
			2.3	0.40		0.8	0.40	0.8	0.40	0.8	
			3.0	0.53		0.87	0.53	0.87	0.53	0.87	
			4.5	0.71		1.04	0.71	1.04	0.71	1.04	
			5.5	0.8		1.2	0.8	1.2	0.8	1.2	
V_{OH}	Minimum High−Level Output Voltage	$V_{IN} \leq V_{T-MIN}$ I_{OH} = −50 μA	1.65 − 5.5	V_{CC} − 0.1			V_{CC} − 0.1		V_{CC} − 0.1		V
		$V_{IN} \leq V_{T-MIN}$									
		I_{OH} = −4 mA	1.65	1.2			1.2		1.2		
		I_{OH} = −8 mA	2.3	1.9			1.9		1.9		
		I_{OH} = −16 mA	3.0	2.4			2.4		2.4		
		I_{OH} = −24 mA	3.0	2.3			2.3		2.3		
		I_{OH} = −32 mA	4.5	3.8			3.8		3.8		
V_{OL}	Maximum Low−Level Output Voltage	$V_{IN} \geq V_{T+MAX}$ I_{OL} = 50 μA	1.65 − 5.5			0.1		0.1		0.1	V
		$V_{IN} \geq V_{T+MAX}$									
		I_{OL} = 4 mA	1.65			0.45		0.45		0.45	
		I_{OL} = 8 mA	2.3			0.3		0.3		0.3	
		I_{OL} = 16 mA	3.0			0.4		0.4		0.4	
		I_{OL} = 24 mA	3.0			0.55		0.55		0.55	
		I_{OL} = 32 mA	4.5			0.55		0.55		0.55	
I_{IN}	Input Leakage Current	$0 \leq V_{IN} \leq$ 5.5 V	0 to 5.5			±0.1		±1.0		±1.0	μA
I_{CC}	Quiescent Supply Current	$0 \leq V_{IN} \leq V_{CC}$	5.5			1.0		10		10	μA

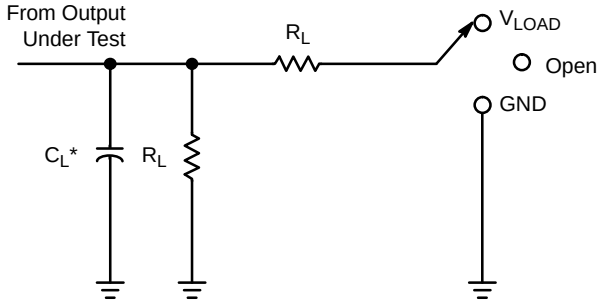
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

Symbol	Parameter	V_{CC} (V)	Test Condition	T_A = 25°C			$T_A \leq$ +85°C		T_A = −55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Propagation Delay, Any Input to Output Y (See Test Circuit)	1.65 − 1.95		3.2	9.0	14.4	3.2	14.4	3.2	14.4	ns
		2.3 − 2.7		2.0	5.3	8.3	2.0	8.3	2.0	8.3	
		3.0 − 3.6		1.5	4.0	6.3	1.5	6.3	1.5	6.3	
		4.5 − 5.5		1.1	3.4	5.1	1.1	5.1	1.1	5.1	
C_{IN}	Input Capacitance				3.5						pF
C_{PD}	Power Dissipation Capacitance (Note 6)	5.0	f = 10 MHz		22						pF

6. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no−load dynamic power consumption: $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

TEST CIRCUIT AND VOLTAGE WAVEFORMS



*C_L includes probes and jig capacitance.

Figure 9. Load Circuit

Test	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	V_{LOAD}
t_{PHZ}/t_{PZH}	GND

V_{CC}	Inputs		V_M	V_{LOAD}	C_L	R_L	V_Δ
	V_I	t_r/t_f					
1.8 V ± 0.15 V	V_{CC}	≤ 2 ns	$V_{CC}/2$	2 x V_{CC}	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V_{CC}	≤ 2 ns	$V_{CC}/2$	2 x V_{CC}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤ 2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5.5 V ± 0.5 V	V_{CC}	≤ 2.5 ns	$V_{CC}/2$	2 x V_{CC}	50 pF	500 Ω	0.3 V

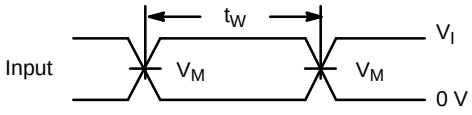


Figure 10. Voltage Waveforms Pulse Duration

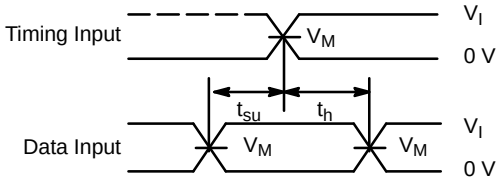


Figure 11. Voltage Waveforms Setup and Hold Times

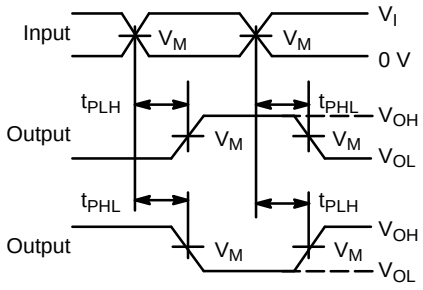


Figure 12. Voltage Waveforms Propagation Delay Times Inverting and Noninverting Outputs

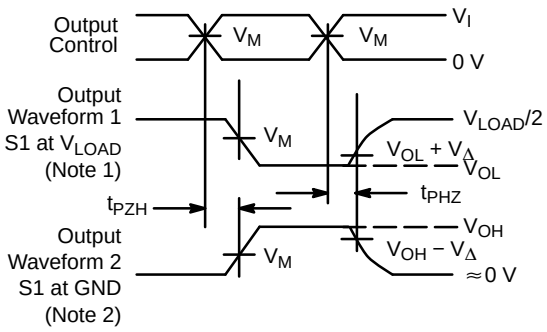


Figure 13. Voltage Waveforms Enable and Disable Times Low− and High−Level Enabling

1. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control.
2. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control
3. All input pulses are supplied by generators having the following characteristics: PRR $\leq$ 10 MHz, Z_O = 50 Ω.
4. The outputs are measured one at a time, with one transition per measurement.
5. All parameters are waveforms are not applicable to all devices.

ORDERING INFORMATION

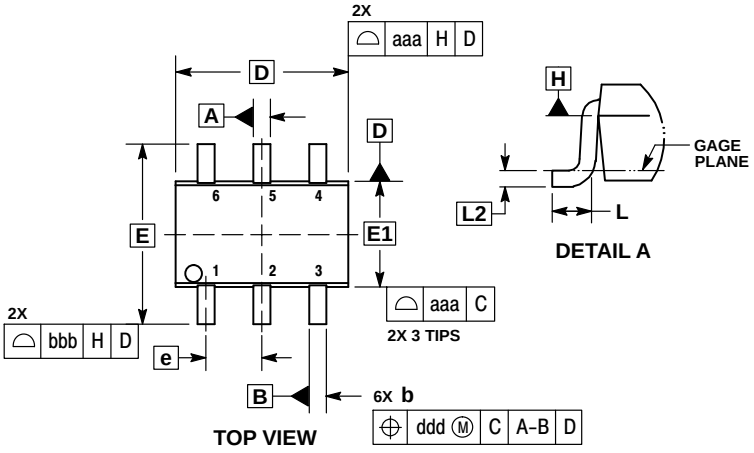
Device	Package	Shipping†
NL7SZ58DFT2G	SC−88 (Pb−Free)	3000 / Tape & Reel
NLV7SZ58DFT2G*	SC−88 (Pb−Free)	3000 / Tape & Reel

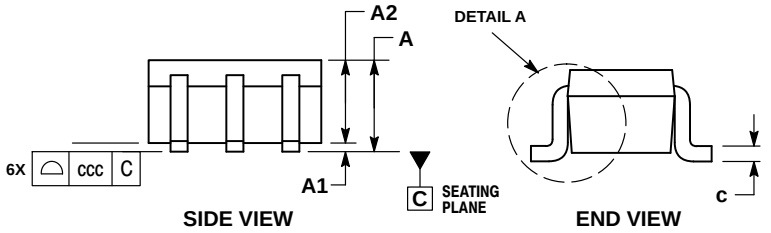
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

PACKAGE DIMENSIONS

SC−88/SC70−6/SOT−363
CASE 419B−02
ISSUE Y

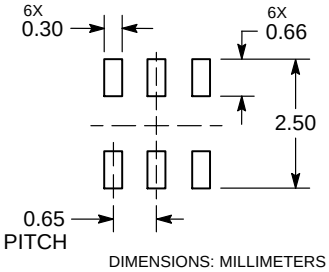




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	−−−	−−−	1.10	−−−	−−−	0.043
A1	0.00	−−−	0.10	0.000	−−−	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

RECOMMENDED SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

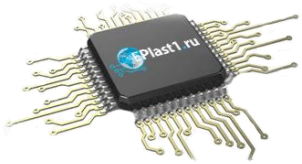
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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